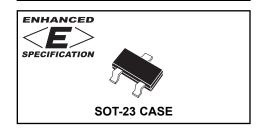
CMPD2836E CMPD2838E

ENHANCED SPECIFICATION

SURFACE MOUNT DUAL SILICON SWITCHING DIODES



The following configurations are available: CMPD2836E DUAL, COMMON ANODE CMPD2838E DUAL, COMMON CATHODE

Semiconductor Corp.

DESCRIPTION:

The Central Semiconductor CMPD2836E and CMPD2838E are Enhanced versions of the CMPD2836 and CMPD2838 High Speed Switching Diodes. These devices are manufactured by the epitaxial planar process, in an epoxy molded surface mount SOT-23 package, designed for high speed switching applications.

FEATURED ENHANCED SPECIFICATIONS:

- ♦ BV_R from 75V min to 120V min.
- lacktriangle V_F from 1.2V max to 1.0V max.

MARKING CODE: CA2E **MARKING CODE: CA6E**

MAXIMUM RATINGS	(T _A =25 °C)
-----------------	-------------------------

	SYMBOL			UNITS	
♦	Peak Repetitive Reverse Voltage	v_{RRM}	120	V	
	Average Forward Current	lO	200	mA	
	Peak Forward Current	^I FM	300	mA	
	Power Dissipation	P_{D}	350	mW	
	Operating and Storage				
	Junction Temperature	T _J ,T _{stg}	-65 to +150	°C	
	Thermal Resistance	$\Theta_{\sf JA}$	357	°C/W	

ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
•	BV_R	I _R =100μA	120	150		V
•	I_{R}	V _R =80V			100	nA
•	v_F	I _F =10mA		0.72	0.85	V
•	V_{F}	I _F =50mA		0.84	0.95	V
•	V_{F}	I _F =100mA		0.92	1.0	V
	c_T	V _R =0, f=1 MHz		1.5	4.0	pF
	t _{rr}	$I_R=I_F=10$ mA, $R_L=100\Omega$, Rec. to 1.0mA			4.0	ns

♦ Enhanced specification.

R1 (20-February 2003)

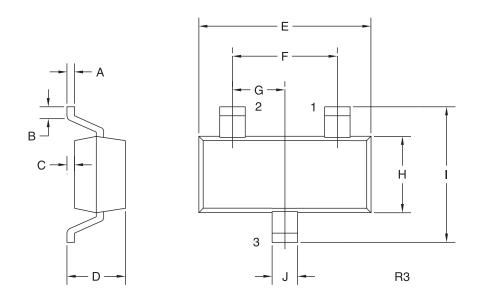


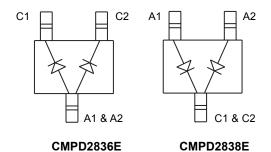
CMPD2836E CMPD2838E

ENHANCED SPECIFICATION

SURFACE MOUNT DUAL SILICON SWITCHING DIODES

SOT-23 CASE - MECHANICAL OUTLINE





MARKING CODE: CA2E MARKING CODE: CA6E

DIMENSIONS				
	INCHES		MILLIMETERS	
SYMBOL	MIN	MAX	MIN	MAX
Α	0.003	0.007	0.08	0.18
В	0.006	-	0.15	-
С	-	0.005	-	0.13
D	0.035	0.043	0.89	1.09
Е	0.110	0.120	2.80	3.05
F	0.075		1.90	
G	0.037		0.95	
Н	0.047	0.055	1.19	1.40
	0.083	0.098	2.10	2.49
J	0.014	0.020	0.35 0.50	

SOT-23 (REV: R3)